BC856...BC860 PNP Silicon Epitaxial Transistor

for switching and amplifier applications



SOT-23 Plastic Package

Absolute Maximum Ratings (T_a = 25 °C)

Parameter		Symbol	Value	Unit
Collector Base Voltage	BC856	-V _{CBO}	80	V
-	BC857, BC860	$-V_{CBO}$	50	V
	BC858, BC859	$-V_{CBO}$	30	V
Collector Emitter Voltage	BC856	-V _{CEO}	65	V
	BC857, BC860	$-V_{CEO}$	45	V
	BC858, BC859	-V _{CEO}	30	V
Emitter Base Voltage		$-V_{EBO}$	5	V
Collector Current		-I _C	100	mA
Peak Collector Current		-I _{CM}	200	mA
Power Dissipation		P _{tot}	200	mW
Junction Temperature		T _j	150	°C
Storage Temperature Range		T_{stg}	- 65 to + 150	°C

DEVICE MARKING

BC856A=3A;BC856B=3B;BC856C=3C; BC857A=3E;BC857B=3F;BC857C=3G; BC858A=3J; BC858B=3H; BC858C=3D BC859A=4A;BC859B=4B;BC859C=4C; BC860A=4E;BC860B=4F;BC860C=4G;

Page 1 of 4 2/24/2012

Characteristics at T_a = 25 °C

Parameter	Symbol	Min.	Max.	Unit
DC Current Gain at $-V_{CE} = 5 \text{ V}$, $-I_C = 2 \text{ mA}$ Current Gain Group AB	h _{FE} h _{FE}	110 200 420	220 450 800	- - -
Collector Base Cutoff Current at -V _{CB} = 30 V	-I _{CBO}	-	15	nA
Collector Base Breakdown Voltage at -I _C = 10 µA BC856 BC857, BC860 BC858, BC858		80 50 30	- - -	V V V
Collector Emitter Breakdown Voltage at $-I_C$ = 10 μ A BC856 BC857, BC860 BC858, BC858		80 50 30	- - -	V V
Collector Emitter Breakdown Voltage at -I _C = 10 mA BC856 BC857, BC860 BC858, BC858		65 45 30	- - -	V V V
Emitter Base Breakdown Voltage at -I _E = 1 µA	-V _{(BR)EBO}	5	-	V
Collector Emitter Saturation Voltage at $-I_C = 10$ mA, $-I_B = 0.5$ mA at $-I_C = 100$ mA, $-I_B = 5$ mA	-V _{CE(sat)} -V _{CE(sat)}	-	0.3 0.65	V
Base Emitter On Voltage at $-I_C = 2$ mA, $-V_{CE} = 5$ V at $-I_C = 10$ mA, $-V_{CE} = 5$ V	-V _{BE(on)} -V _{BE(on)}	0.6	0.75 0.82	V
Current Gain Bandwidth Product at $-V_{CE} = 5 \text{ V}$, $-I_{C} = 10 \text{ mA}$, $f = 100 \text{ MHz}$	f _T	100	-	MHz
Output Capacitance at -V _{CB} = 10 V, f = 1 MHz	C _{ob}	-	6	pF
Noise Figure at -I _C = 200 μA, -V _{CE} = 5 V, BC856, BC857, BC858 R _G = 2 KΩ, f = 1 KHz BC859, BC860 at -I _C = 200 μA, -V _{CE} = 5 V, BC859 R _G = 2 KΩ, f = 30 ~15 KHz BC860	NF	- - -	10 4 4 2	dB

Page 2 of 4

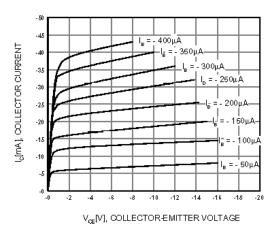


Figure 1. Static Characteristic

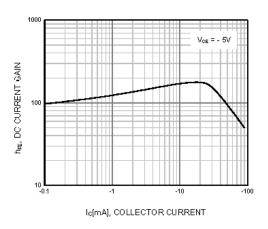


Figure 2. DC current Gain

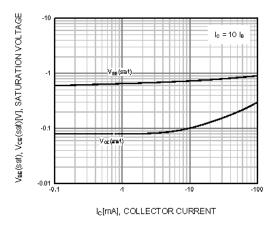


Figure 3. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage

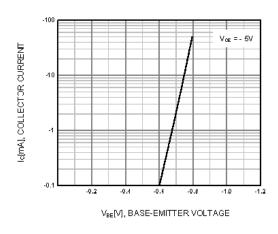


Figure 4. Base-Emitter On Voltage

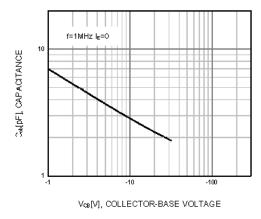


Figure 5. Collector Output Capacitance

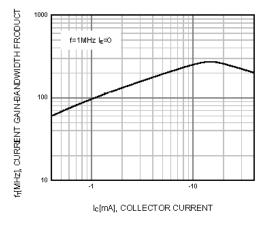


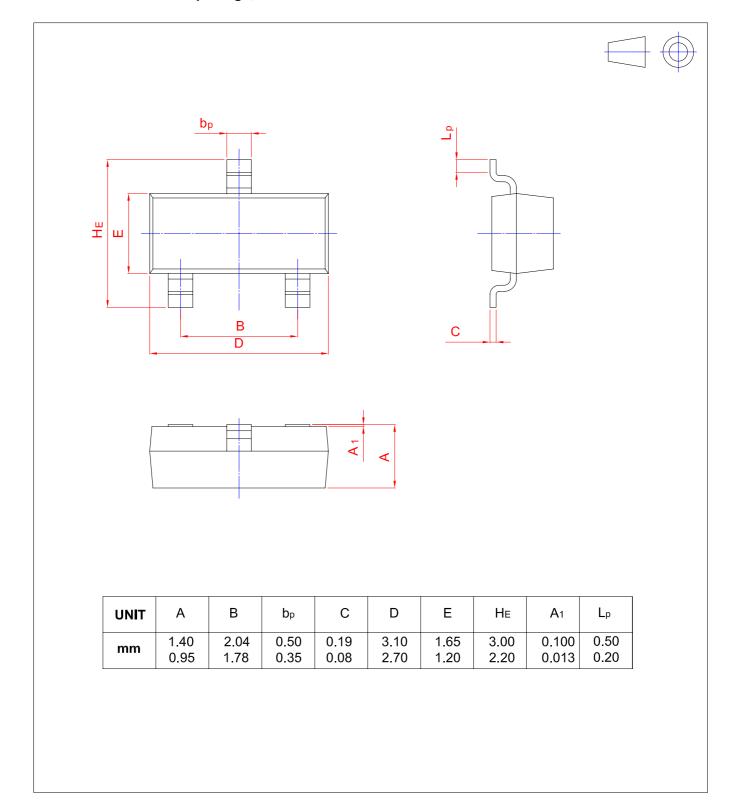
Figure 6. Current Gain Bandwidth Product

Page 3 of 4

PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT-23



Page 4 of 4

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for Bipolar Transistors - BJT category:

Click to view products by Hong Kong Chuangji manufacturer:

Other Similar products are found below:

619691C MCH4017-TL-H MMBT-2369-TR BC546/116 BC557/116 BSW67A NJVMJD148T4G NTE123AP-10 NTE153MCP NTE16

NTE195A NTE92 2N4401-A 2N6728 2SA1419T-TD-H 2SA2126-E 2SB1204S-TL-E 2SC2712S-GR,LF SP000011176 2N2907A 2N3904
NS 2N5769 2SC2412KT146S CPH6501-TL-E MCH4021-TL-E MJE340 Jantx2N5416 US6T6TR NJL0281DG 732314D CPH3121-TL-E

CPH6021-TL-H 873787E IMZ2AT108 MMST8098T146 UMX21NTR MCH6102-TL-E NJL0302DG 30A02MH-TL-E NTE13 NTE26

NTE282 NTE323 NTE350 NTE81 STX83003-AP JANTX2N2920L JANSR2N2222AUB CMLT3946EG TR 2SA1371D-AE